

**LISTING OF THE CLAIMS**

1. (Previously Presented) A semiconductor polishing composition comprising:  
fumed silica, the semiconductor polishing composition being an aqueous  
dispersion solution of fumed silica,  
wherein an increase rate of average particle diameter of fumed silica after  
a shake test for 10 days is 10% or less.
2. (Original) The semiconductor polishing composition of claim 1, wherein a  
content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the  
composition.
3. (Previously Presented) The semiconductor polishing composition of claim 1,  
wherein the average particle diameter of the fumed silica is in a range of 70 to 110 nm.
4. (Previously Presented) The semiconductor polishing composition of claim 1,  
wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica  
dispersion solution to an alkali aqueous solution.
5. (Original) The semiconductor polishing composition of claim 4, wherein a pH of  
the alkali aqueous solution is in a range of 12 to 14.

6. (Previously Presented) The semiconductor polishing composition of claim 2, wherein the average particle diameter of the fumed silica is in a range of 70 to 110 nm.

7. (Previously Presented) The semiconductor polishing composition of claim 2, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

8. (Previously Presented) The semiconductor polishing composition of claim 3, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

9. (Previously Presented) The semiconductor polishing composition of claim 6, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

10. (Previously Presented) The semiconductor polishing composition of claim 7, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.

11. (Previously Presented) The semiconductor polishing composition of claim 8, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.

12. (Previously Presented) The semiconductor polishing composition of claim 9, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.